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ning of each regular issue of the PCT Gazette.

(54) Title: ORGANIC SILICATE POLYMER AND INSULATION FILM COMPRISING THE SAME

(57) **Abstract:** The present invention relates to a composition for forming a low dielectric insulating film for a semiconductor device, particularly to an organosilicate polymer prepared by mixing a thermally decomposable organic silane compound that is capped with a silane compound at both its ends, and a common silane compound or silane oligomer, and then adding water and a catalyst to conduct hydrolysis and condensation, as well as to a coating composition for an insulating film for a semiconductor device comprising the same, a coating composition for an insulating film for a semiconductor device further comprising a pore-forming organic substance, a method for preparing an insulating film for a semiconductor device by coating the composition and curing, and a semiconductor device comprising a low dielectric insulating film prepared by the method. The organosilicate polymer prepared according to the present invention has superior thermal stability and mechanical strength; an insulating film-forming composition comprising the same can be used for an interlayer insulating film for low dielectric wiring that can contribute to a high speed semiconductor, reduce power consumption, and remarkably decrease cross-talk between metal wiring; and a film obtained by applying the composition to an insulating film has superior coating properties, inhibits phase-separation, can easily control minute pores because organic substances are thermally decomposed to form pores during a curing process, and has superior insulating properties and a remarkably decreased film density.

WO 2004/003059 A1